Low-power unbuffered inverter Rev. 5 — 29 June 2012

Product data sheet

1. **General description**

The 74AUP1GU04 provides the single unbuffered inverting gate.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

Features and benefits 2.

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

Ordering information 3.

Table 1. Orderin	g information			
Type number	Package			
	Temperature range	Name	Description	Version
74AUP1GU04GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74AUP1GU04GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886
74AUP1GU04GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891
74AUP1GU04GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115
74AUP1GU04GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202
74AUP1GU04GX	–40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body $0.8 \times 0.8 \times 0.35$ mm	SOT1226



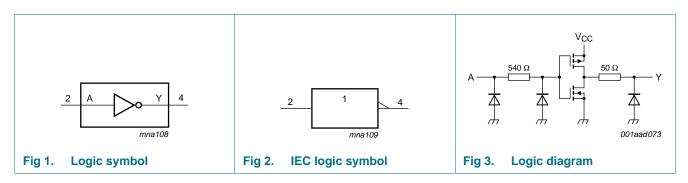
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4. Marking

Table 2. Marking	
Type number	Marking code ^[1]
74AUP1GU04GW	pD
74AUP1GU04GM	pD
74AUP1GU04GF	pD
74AUP1GU04GN	pD
74AUP1GU04GS	pD
74AUP1GU04GX	pD

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



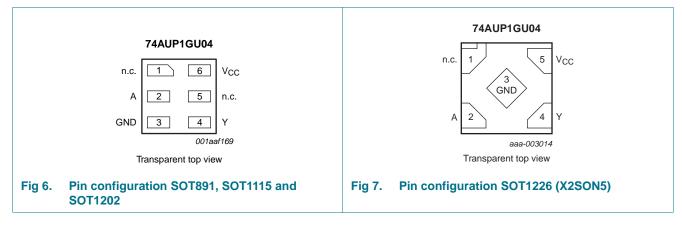
6. Pinning information

6.1 Pinning



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6.2 Pin description

Table 3. Pin description								
Symbol	Pin		Description					
	TSSOP5 and X2SON5	XSON6						
n.c.	1	1	not connected					
А	2	2	data input					
GND	3	3	ground (0 V)					
Y	4	4	data output					
n.c.	-	5	not connected					
V _{CC}	5	6	supply voltage					

7. Functional description

Table 4.	Function table ^[1]	
Input		Output
Α		Y
L		Н
Н		L

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

			0	.0	,
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage		<u>[1]</u> –0.5	V _{CC} + 0.5	V
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	±20	mA
I _{CC}	supply current		-	+50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to +125 \ ^{\circ}C$	[2] _	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP5 packages: above 87.5 °C the value of Ptot derates linearly with 4.0 mW/K.

For XSON6 and X2SON5 packages: above 118 °C the value of Ptot derates linearly with 7.8 mW/K.

9. Recommended operating conditions

V_{CC} supply voltage0.83.6V V_{I} input voltage03.6V V_{O} output voltage0 V_{CC} V T_{amb} ambient temperature-40+125°C	Table 0.	Recommended operating conditi	0115			
	Symbol	Parameter	Conditions	Min	Max	Unit
V_O output voltage0 V_{CC} V T_{amb} ambient temperature-40+125°C	V _{CC}	supply voltage		0.8	3.6	V
T_{amb} ambient temperature -40 +125 °C	VI	input voltage		0	3.6	V
	Vo	output voltage		0	V_{CC}	V
$\Delta t / \Delta V$ input transition rise and fall rate $V_{CC} = 0.8 V$ to 3.6 V 0 200 ns.	T _{amb}	ambient temperature		-40	+125	°C
	$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 V \text{ to } 3.6 V$	0	200	ns/V

Table 6. Recommended operating conditions

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
VIH	HIGH-level input voltage	V_{CC} = 0.8 V to 3.6 V	$0.75 \times V_{CC}$	-	-	V
VIL	LOW-level input voltage	$V_{CC} = 0.8 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	$0.25\times V_{CC}$	V
V _{OH}	HIGH-level output voltage	I_{O} = –20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		I_{O} = -2.3 mA; V_{CC} = 2.3 V	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		I_{O} = -4.0 mA; V_{CC} = 3.0 V	2.6	-	-	V
V _{OL}	LOW-level output voltage	I_O = 20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		$I_{O} = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3\times V_{CC}$	V
		I_{O} = 1.7 mA; V_{CC} = 1.4 V	-	-	0.31	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		I_{O} = 4.0 mA; V_{CC} = 3.0 V	-	-	0.44	V
l _l	input leakage current	V_{I} = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.1	μΑ
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = O \ A; \\ V_{CC} = O.8 \ V \ to \ 3.6 \ V \end{array}$	-	-	0.5	μA
CI	input capacitance	V_{CC} = 0 V to 3.6 V; V_{I} = GND or V_{CC}	-	1.5	-	pF
Co	output capacitance	$V_{O} = GND; V_{CC} = 0 V$	-	1.8	-	pF
T _{amb} = –	40 °C to +85 °C					
VIH	HIGH-level input voltage	$V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 0.8 V to 3.6 V	-	-	$0.25\times V_{CC}$	V
V _{ОН}	HIGH-level output voltage	I_{O} = –20 $\mu\text{A};~V_{CC}$ = 0.8 V to 3.6 V	$V_{CC} - 0.1$	-	-	V
		$I_0 = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		I_{O} = -2.3 mA; V_{CC} = 2.3 V	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7$ mA; $V_{CC} = 3.0$ V	2.67	-	-	V
		$I_0 = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OL}	LOW-level output voltage	I_{O} = 20 $\mu A;$ V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3\times V_{CC}$	V
		I_{O} = 1.7 mA; V_{CC} = 1.4 V	-	-	0.37	V
		I_{O} = 1.9 mA; V_{CC} = 1.65 V	-	-	0.35	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.33	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
l _l	input leakage current	V_{I} = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.5	μΑ
I _{CC}	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μA
T _{amb} = -	40 °C to +125 °C					
VIH	HIGH-level input voltage	V_{CC} = 0.8 V to 3.6 V	$0.75 \times V_{CC}$	-	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 0.8 V to 3.6 V	-	-	$0.25\times V_{CC}$	V
V _{OH}	HIGH-level output voltage	I_O = –20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	V _{CC} - 0.11	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6 \times V_{\text{CC}}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_0 = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V _{OL}	LOW-level output voltage	I_{O} = 20 $\mu A;$ V_{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		$I_0 = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.33 \times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		I_{O} = 3.1 mA; V_{CC} = 2.3 V	-	-	0.50	V
		I_{O} = 2.7 mA; V_{CC} = 3.0 V	-	-	0.36	V
		I_{O} = 4.0 mA; V_{CC} = 3.0 V	-	-	0.50	V
l _l	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.75	μΑ
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ

Static characteristics ... continued Table 7.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9

Symbo	Parameter	Conditions			25 °C		-40	°C to +1	25 °C	Unit
				Min	Typ <mark>[1]</mark>	Мах	Min	Max (85 °C)	Max (125 °C)	
C _L = 5	pF									
pd	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	6.2	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		0.9	2.3	4.4	0.9	4.8	5.3	ns
		V_{CC} = 1.4 V to 1.6 V		0.7	1.7	3.1	0.6	3.4	3.8	ns
		V_{CC} = 1.65 V to 1.95 V		0.5	1.4	2.6	0.5	2.9	3.2	ns
		V_{CC} = 2.3 V to 2.7 V		0.4	1.1	2.0	0.4	2.3	2.6	ns
		V_{CC} = 3.0 V to 3.6 V		0.3	1.0	1.8	0.3	2.1	2.4	ns
C _L = 10) pF									
pd	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	9.6	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		1.2	3.1	6.1	1.2	6.8	7.5	ns
		V_{CC} = 1.4 V to 1.6 V		1.0	2.3	4.0	0.9	4.6	5.1	ns
		V_{CC} = 1.65 V to 1.95 V		0.8	1.9	3.3	0.7	3.8	4.2	ns
		V_{CC} = 2.3 V to 2.7 V		0.6	1.5	2.7	0.6	3.1	3.5	ns
		V_{CC} = 3.0 V to 3.6 V		0.5	1.3	2.4	0.5	2.7	3.0	ns
C _L = 15	5 pF									
pd	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	13.0	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		1.6	3.8	7.9	1.4	8.8	9.7	ns
		V_{CC} = 1.4 V to 1.6 V		1.3	2.8	4.9	1.1	5.7	6.3	ns
		V_{CC} = 1.65 V to 1.95 V		1.0	2.3	4.0	0.9	4.7	5.2	ns
		V_{CC} = 2.3 V to 2.7 V		0.8	1.9	3.2	0.8	3.7	4.1	ns
		V_{CC} = 3.0 V to 3.6 V		0.7	1.6	2.9	0.7	3.3	3.7	ns
C _L = 30) pF									
pd	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	23.2	-	-	-	-	-
		V_{CC} = 1.1 V to 1.3 V		2.4	6.0	13.1	2.2	14.8	16.3	ns
		V_{CC} = 1.4 V to 1.6 V		2.0	4.2	7.6	1.8	9.0	9.9	ns
		V_{CC} = 1.65 V to 1.95 V		1.7	3.6	6.1	1.5	7.2	8.0	ns
		V_{CC} = 2.3 V to 2.7 V		1.4	2.9	4.8	1.3	5.7	6.3	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.2	2.5	4.3	1.1	5.1	5.7	ns

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Symbol	Parameter	Conditions	25 °C		–40 °C to +125 °C			Unit	
			Min	Typ <mark>[1]</mark>	Мах	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pl	F, 10 pF, 15 pF and	30 pF					1		
C _{PD}	power dissipation capacitance	$f = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$ [3]							
		$V_{CC} = 0.8 V$	-	1.2	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	-	1.1	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	-	1.2	-	-	-	-	pF
		V_{CC} = 1.65 V to 1.95 V	-	1.4	-	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V	-	2.8	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	4.4	-	-	-	-	pF

Table 8. Dynamic characteristics ... continued

[1] All typical values are measured at nominal V_{CC} .

[2] t_{pd} is the same as t_{PLH} and t_{PHL}

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $\label{eq:PD} \mathsf{P}_{\mathsf{D}} = C_{\mathsf{PD}} \times \mathsf{V}_{\mathsf{CC}}{}^2 \times f_i \times \mathsf{N} + \Sigma(C_\mathsf{L} \times \mathsf{V}_{\mathsf{CC}}{}^2 \times f_o) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms

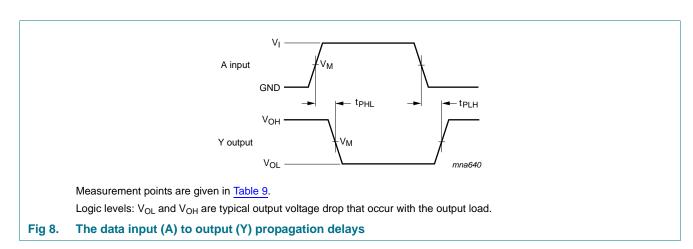


Table 9. **Measurement points**

Supply voltage	Output	Input				
V _{CC}	V _M	V _M	VI	$t_r = t_f$		
0.8 V to 3.6 V	$0.5 imes V_{CC}$	$0.5\times V_{CC}$	V _{CC}	≤ 3.0 ns		

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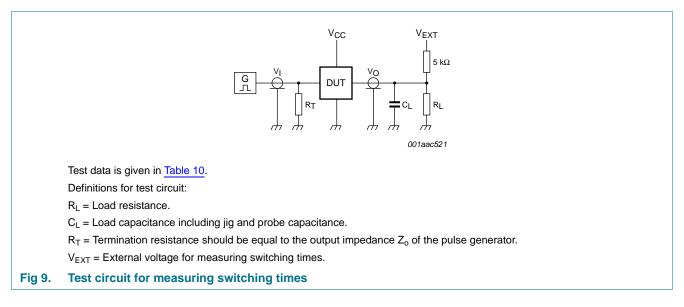


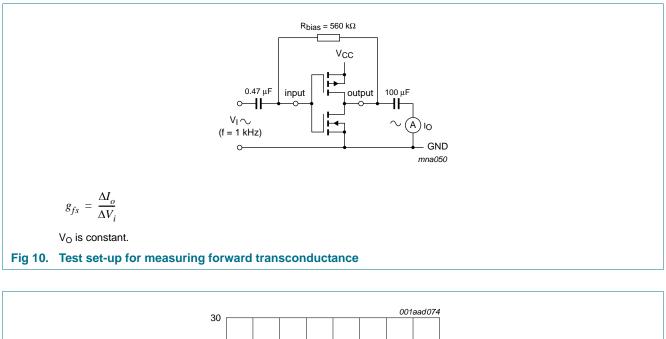
Table 10. Test data

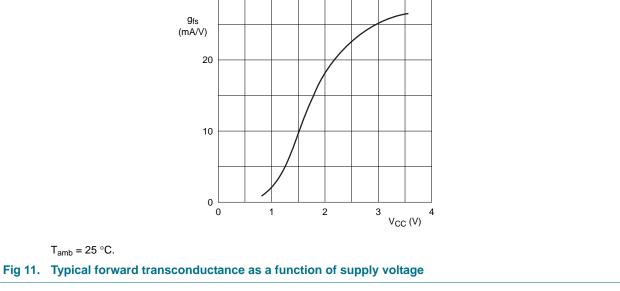
Supply voltage	Load	V _{EXT}			
V _{cc}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times $R_L = 5 k\Omega$, for measuring propagation delays, setup and hold times and pulse width $R_L = 1 M\Omega$.

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13. Additional characteristics



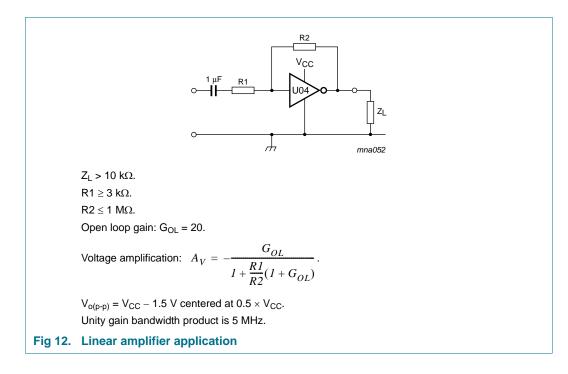


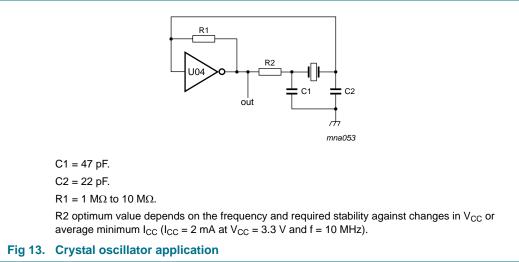
14. Application information

Some applications for the 74AUP1GU04 are:

- Linear amplifier (see Figure 12)
- Crystal oscillator (see Figure 13).

Remark: All values given are typical values unless otherwise specified.





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15. Package outline

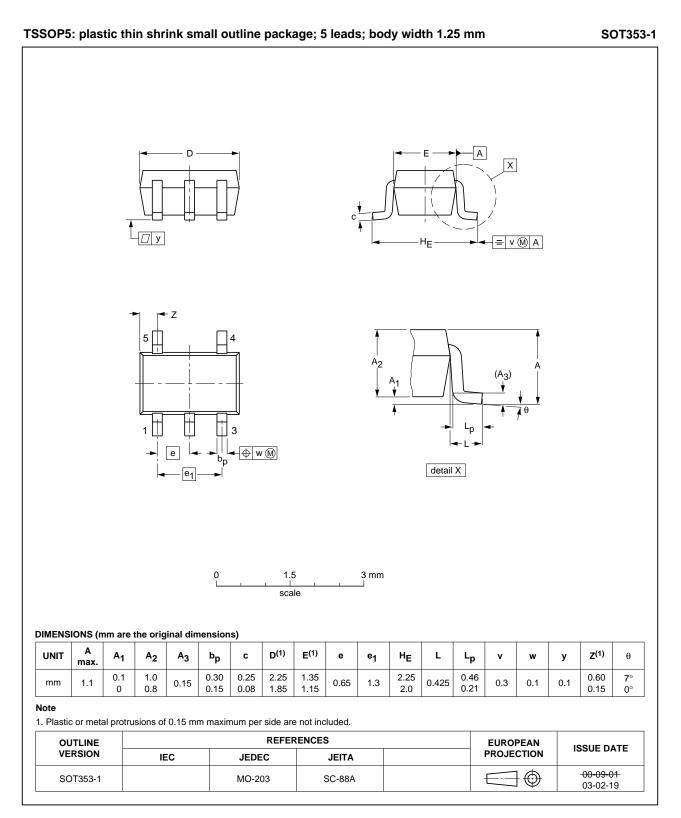


Fig 14. Package outline SOT353-1 (TSSOP5)

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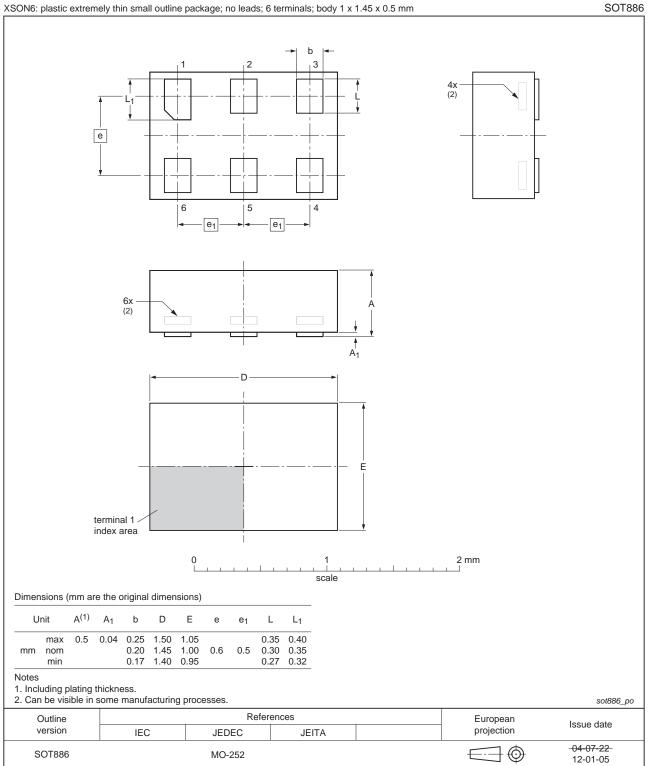


Fig 15. Package outline SOT886 (XSON6)

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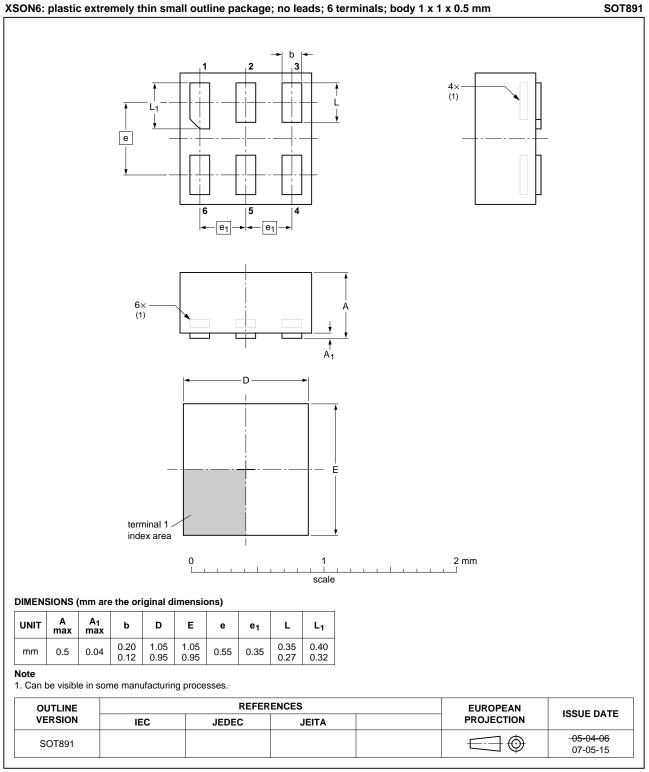
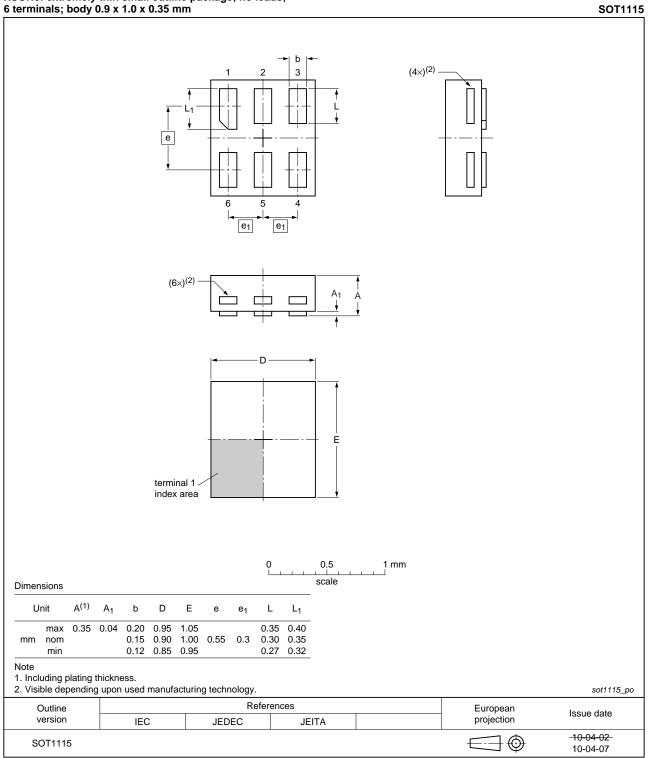


Fig 16. Package outline SOT891 (XSON6)

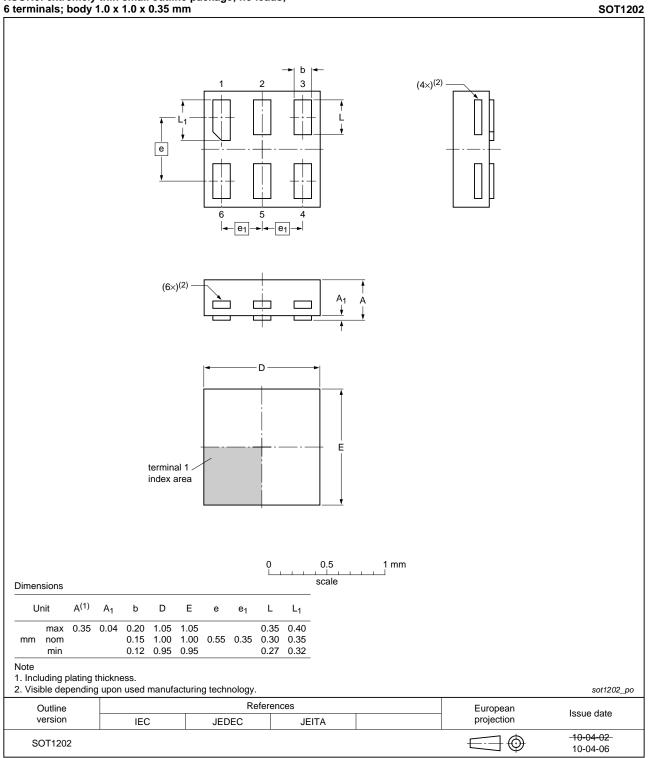
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XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 17. Package outline SOT1115 (XSON6)

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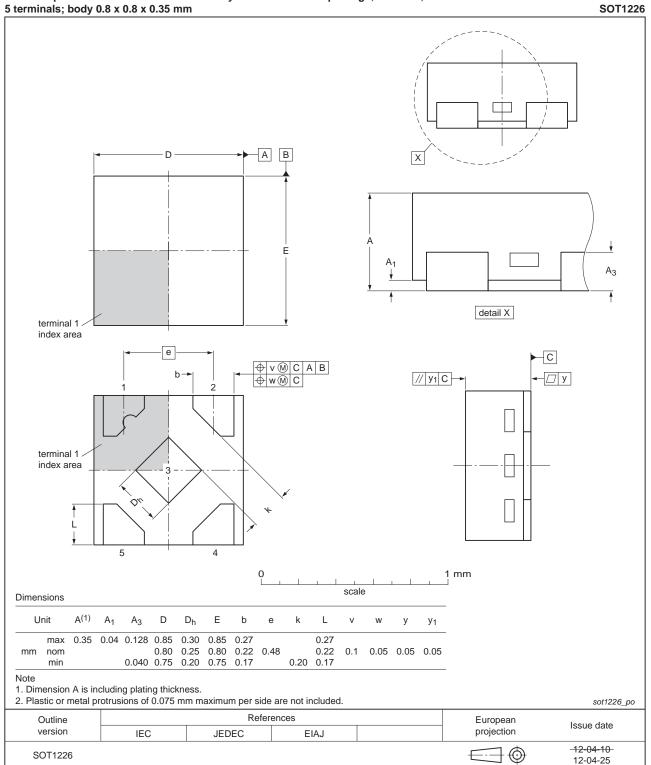


XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 18. Package outline SOT1202 (XSON6)

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X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body 0.8 x 0.8 x 0.35 mm

Fig 19. Package outline SOT1226 (X2SON5)

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16. Abbreviations

Table 11. Abbreviations				
Acronym	Description			
CDM	Charged Device Model			
DUT	Device Under Test			
ESD	ElectroStatic Discharge			
HBM	Human Body Model			
MM	Machine Model			

17. Revision history

Table 12. Revisio	n history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1GU04 v.5	20120629	Product data sheet	-	74AUP1GU04 v.4
Modifications:	 Added type r 	number 74AUP1GU04GX (SC	DT1226)	
	 Package out 	line drawing of SOT886 (Figu	re 15) modified.	
74AUP1GU04 v.4	20111116	Product data sheet	-	74AUP1GU04 v.3
Modifications:	 Legal pages 	updated.		
	 Package out 	line drawing SOT363 replace	d by SOT353-1.	
74AUP1GU04 v.3	20100721	Product data sheet	-	74AUP1GU04 v.2
74AUP1GU04 v.2	20060803	Product data sheet	-	74AUP1GU04 v.1
74AUP1GU04 v.1	20050810	Product data sheet	-	-

18. Legal information

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Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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